

# 74AUP1G132

Low-power 2-input NAND Schmitt trigger

Rev. 5 — 29 June 2012

Product data sheet

## 1. General description

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The 74AUP1G132 provides the single 2-input NAND Schmitt trigger function which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage  $V_H$ .

## 2. Features and benefits

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- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40 \text{ }^\circ\text{C}$  to  $+85 \text{ }^\circ\text{C}$  and  $-40 \text{ }^\circ\text{C}$  to  $+125 \text{ }^\circ\text{C}$

## 3. Applications

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- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator.



## 4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1G132GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G132GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G132GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AUP1G132GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1G132GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1G132GX	-40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.35 mm	SOT1226

## 5. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1G132GW	aE
74AUP1G132GM	aE
74AUP1G132GF	aE
74AUP1G132GN	aE
74AUP1G132GS	aE
74AUP1G132GX	aE

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 6. Functional diagram

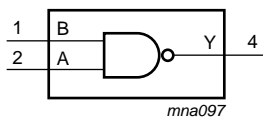


Fig 1. Logic symbol

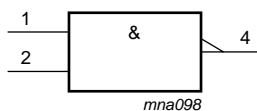


Fig 2. IEC logic symbol

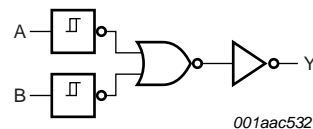


Fig 3. Logic diagram

## 7. Pinning information

### 7.1 Pinning

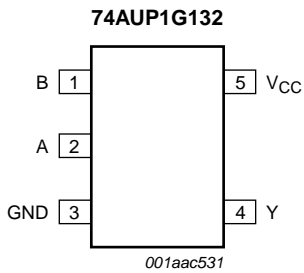


Fig 4. Pin configuration SOT353-1

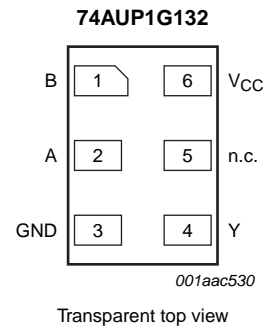


Fig 5. Pin configuration SOT886

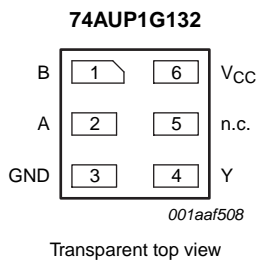


Fig 6. Pin configuration SOT891, SOT1115 and SOT1202

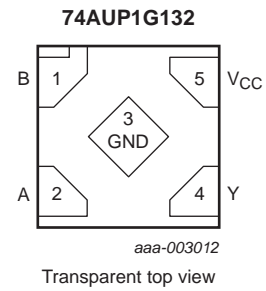


Fig 7. Pin configuration SOT1226 (X2SON5)

### 7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
B	1	1	data input
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

## 8. Functional description

Table 4. Function table<sup>[1]</sup>

Input		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+4.6	V
$I_{OK}$	output clamping current	$V_O < 0$ V	-50	-	mA
$V_O$	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	$\pm 20$	mA
$I_{CC}$	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

For XSON6 and X2SON5 packages: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C

## 11. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<a href="#">[1]</a> -	-	40	μA
C <sub>I</sub>	input capacitance	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 0 V to 3.6 V	-	1.1	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.7	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.55	-	-	V

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.45	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.6	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<a href="#">[1]</a> -	-	50	μA
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.6 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.30	-	-	V		
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.75	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	$\pm 0.75$	$\mu$ A
$I_{CC}$	supply current	$V_I = GND$ or $V_{CC}$ ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	1.4	$\mu$ A
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	75	$\mu$ A

[1] One input at  $V_{CC} - 0.6$  V, other input at  $V_{CC}$  or GND.

## 12. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 9](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	

### $C_L = 5$ pF

$t_{pd}$	propagation delay	A or B to Y; see <a href="#">Figure 8</a>	[2]						
		$V_{CC} = 0.8$ V	-	22.5	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.6	6.3	13.4	2.4	15.1	16.6	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.2	4.6	8.2	1.9	9.7	10.7	ns
		$V_{CC} = 1.65$ V to 1.95 V	1.9	3.9	6.6	1.7	7.9	8.7	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.7	3.2	5.3	1.5	6.2	6.8	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.6	2.9	4.7	1.4	5.6	6.2	ns

### $C_L = 10$ pF

$t_{pd}$	propagation delay	A or B to Y; see <a href="#">Figure 8</a>	[2]						
		$V_{CC} = 0.8$ V	-	26.1	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	3.0	7.2	15.4	2.7	17.3	19.0	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.5	5.2	9.3	2.2	11.0	12.1	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.3	4.5	7.5	2.0	9.0	9.9	ns
		$V_{CC} = 2.3$ V to 2.7 V	2.1	3.8	6.1	1.8	7.2	7.9	ns
		$V_{CC} = 3.0$ V to 3.6 V	2.0	3.5	5.5	1.8	6.5	7.2	ns

### $C_L = 15$ pF

$t_{pd}$	propagation delay	A or B to Y; see <a href="#">Figure 8</a>	[2]						
		$V_{CC} = 0.8$ V	-	29.6	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	3.3	8.0	17.2	3.0	19.4	21.3	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.8	5.8	10.4	2.5	12.3	13.5	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.6	5.0	8.3	2.3	10.0	11.0	ns
		$V_{CC} = 2.3$ V to 2.7 V	2.3	4.2	6.7	2.1	7.9	8.7	ns
		$V_{CC} = 3.0$ V to 3.6 V	2.2	3.9	6.1	2.0	7.3	8.0	ns

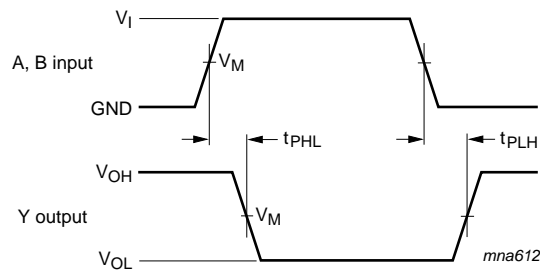
### $C_L = 30$ pF

**Table 8. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 9](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
t <sub>pd</sub>	propagation delay	A or B to Y; see <a href="#">Figure 8</a> <sup>[2]</sup>							
		V <sub>CC</sub> = 0.8 V	-	39.9	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.3	10.2	22.6	3.8	25.4	27.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.6	7.3	13.3	3.2	15.8	17.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.2	6.3	10.6	2.9	12.8	14.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.0	5.3	8.5	2.7	10.1	11.1	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.8	5.0	7.8	2.7	9.2	10.1	ns
<b>C<sub>L</sub> = 5 pF, 10 pF, 15 pF and 30 pF</b>									
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; <sup>[3]</sup> V <sub>I</sub> = GND to V <sub>CC</sub>							
		V <sub>CC</sub> = 0.8 V	-	2.6	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.2	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.8	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.4	-	-	-	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

### 13. Waveforms



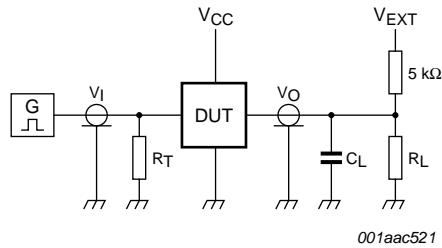
Measurement points are given in [Table 9](#).  
 Logic levels: V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage drop that occur with the output load.

**Fig 8. The data input (A or B) to output (Y) propagation delays**



Table 9. Measurement points

Supply voltage	Output	Input		
$V_{CC}$	$V_M$	$V_M$	$V_I$	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{CC}$	$\leq 3.0$ ns



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5$  kΩ, for measuring propagation delays, setup and hold times and pulse width  $R_L = 1$  MΩ.

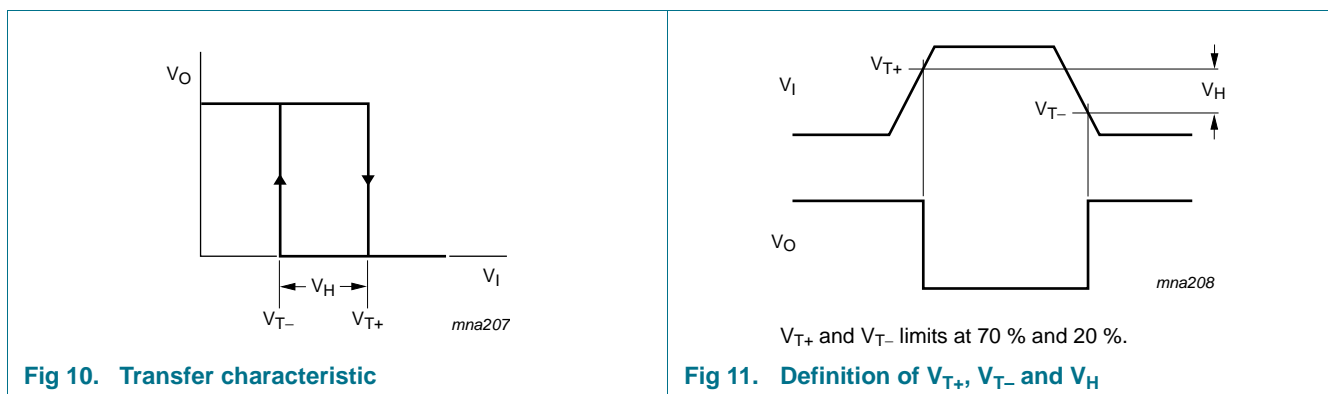
### 14. Transfer characteristics

**Table 11. Transfer characteristics**

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 9](#).)

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V <sub>T+</sub>	positive-going threshold voltage	see <a href="#">Figure 10</a> and <a href="#">Figure 11</a>							
		V <sub>CC</sub> = 0.8 V	0.30	-	0.60	0.30	0.60	0.62	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.90	0.53	0.90	0.92	V
		V <sub>CC</sub> = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		V <sub>CC</sub> = 2.3 V	1.37	-	1.77	1.37	1.77	1.80	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.29	1.88	2.29	2.32	V
V <sub>T-</sub>	negative-going threshold voltage	see <a href="#">Figure 10</a> and <a href="#">Figure 11</a>							
		V <sub>CC</sub> = 0.8 V	0.10	-	0.60	0.10	0.60	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		V <sub>CC</sub> = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V
		V <sub>CC</sub> = 3.0 V	0.88	-	1.24	0.88	1.24	1.24	V
V <sub>H</sub>	hysteresis voltage (V <sub>T+</sub> - V <sub>T-</sub> ); see <a href="#">Figure 10</a> , <a href="#">Figure 11</a> , <a href="#">Figure 12</a> and <a href="#">Figure 13</a>	V <sub>CC</sub> = 0.8 V	0.07	-	0.50	0.07	0.50	0.50	V
		V <sub>CC</sub> = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		V <sub>CC</sub> = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V
		V <sub>CC</sub> = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		V <sub>CC</sub> = 2.3 V	0.53	-	0.92	0.53	0.92	0.92	V
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	0.79	1.31	1.31	V

### 15. Waveforms transfer characteristics



**Fig 10. Transfer characteristic**

**Fig 11. Definition of V<sub>T+</sub>, V<sub>T-</sub> and V<sub>H</sub>**

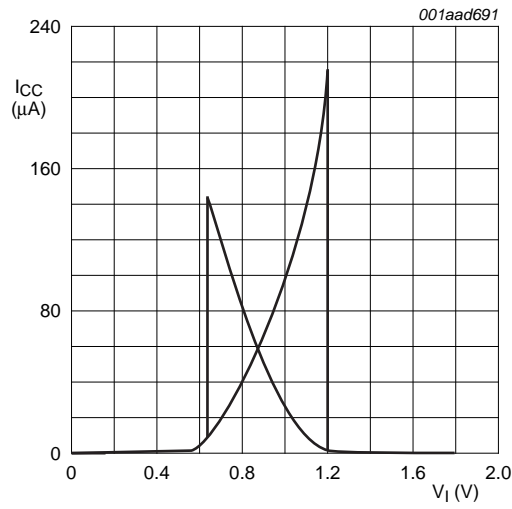


Fig 12. Typical transfer characteristics;  $V_{CC} = 1.8 V$

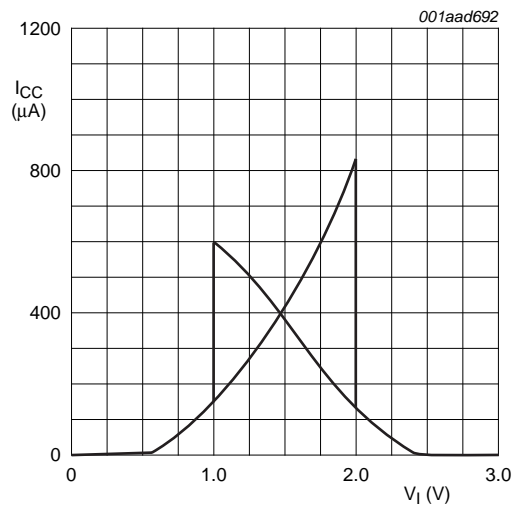


Fig 13. Typical transfer characteristics;  $V_{CC} = 3.0 V$

## 16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

$$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$$

$P_{add}$  = additional power dissipation ( $\mu\text{W}$ );

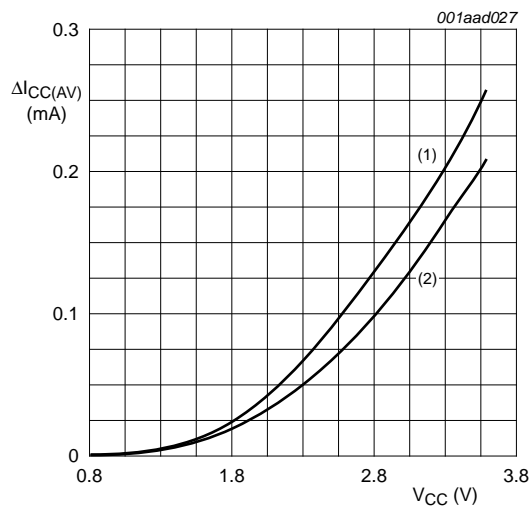
$f_i$  = input frequency (MHz);

$t_r$  = input rise time (ns); 10 % to 90 %;

$t_f$  = input fall time (ns); 90 % to 10 %;

$\Delta I_{CC(AV)}$  = average additional supply current ( $\mu\text{A}$ ).

Average  $\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in [Figure 14](#).



- (1) Positive-going edge.
- (2) Negative-going edge.

Linear change of  $V_I$  between 0.8 V and 2.0 V. All values given are typical, unless otherwise specified.

**Fig 14. Average  $I_{CC}$  as a function of  $V_{CC}$**

17. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

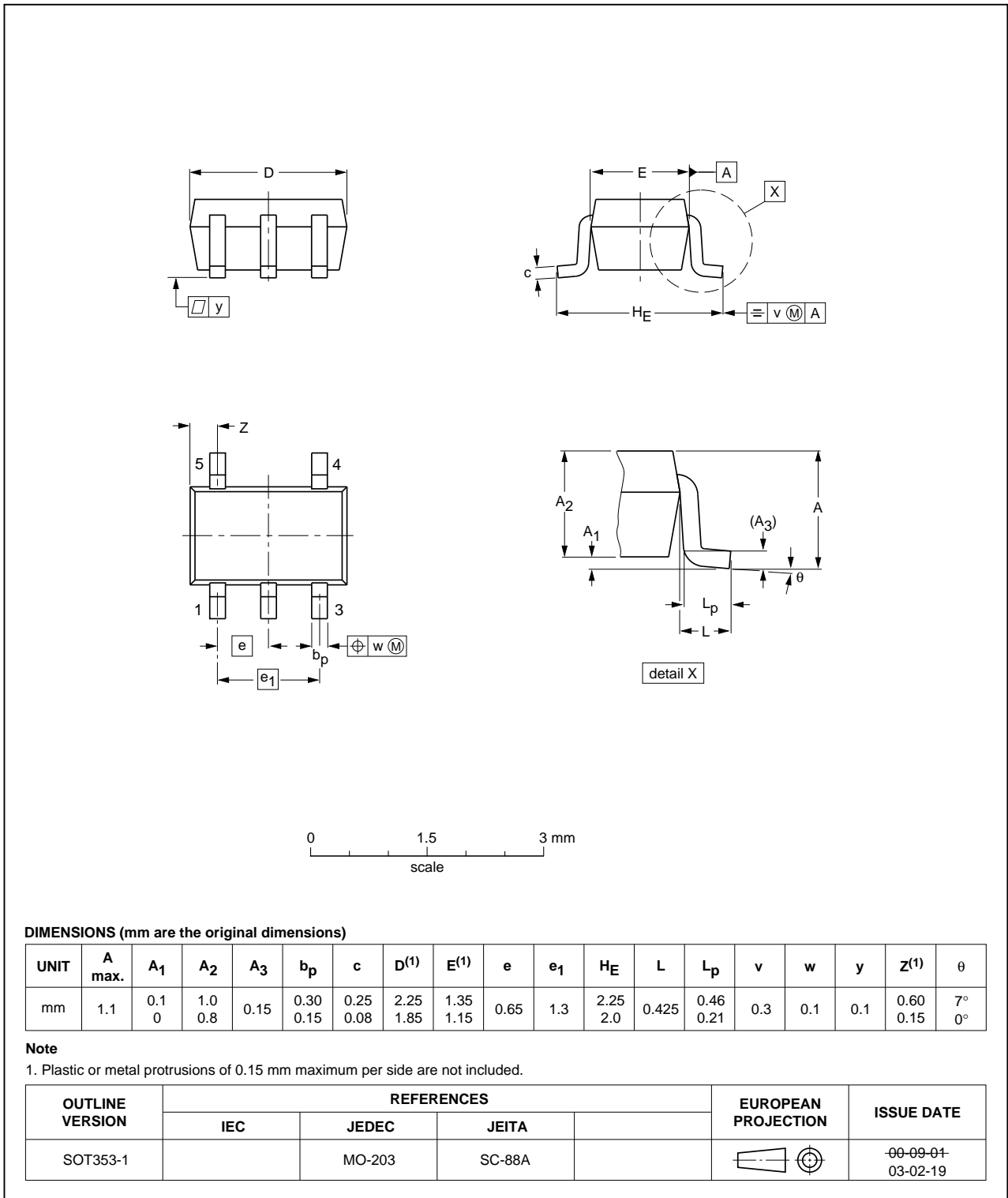


Fig 15. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

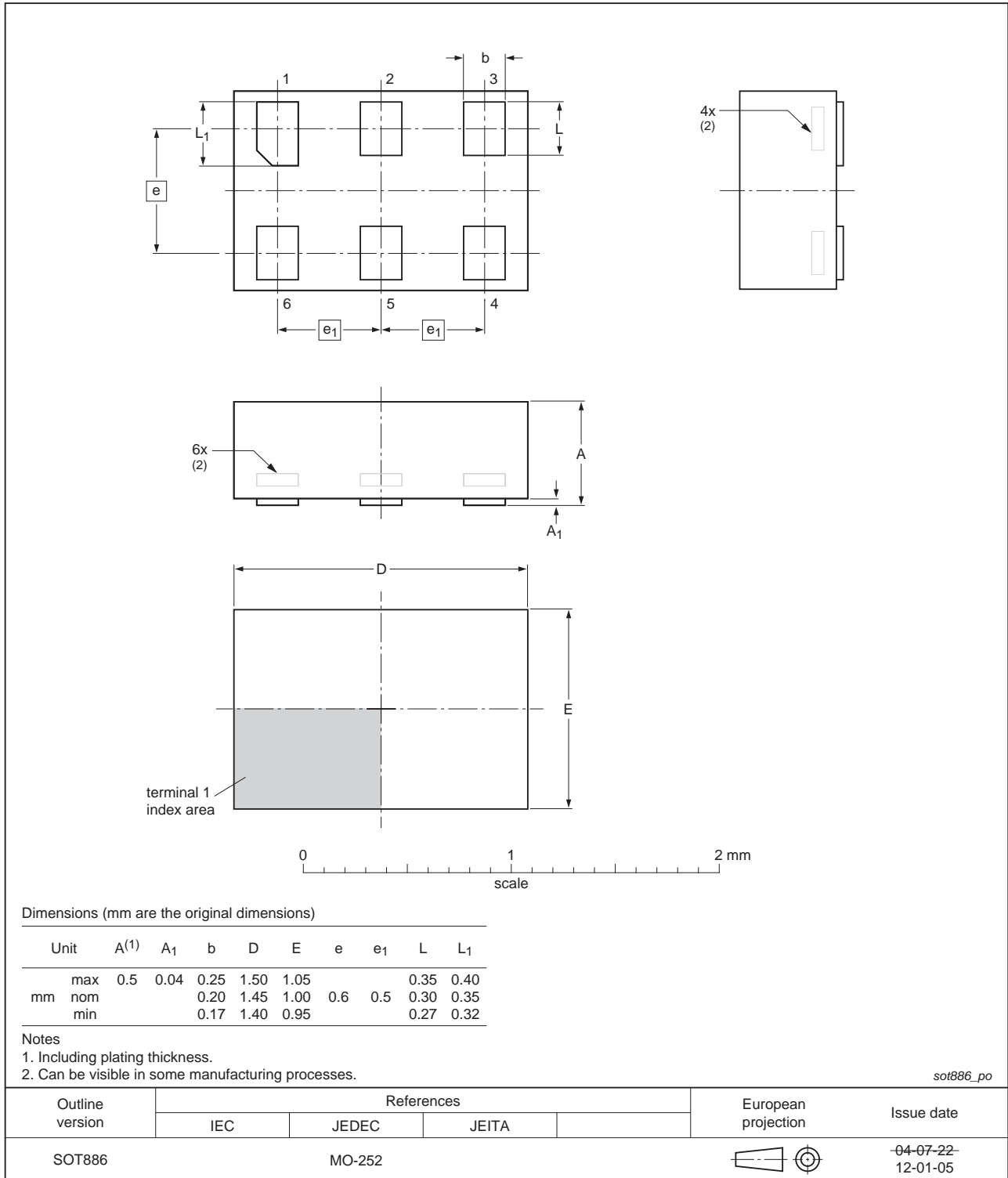


Fig 16. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

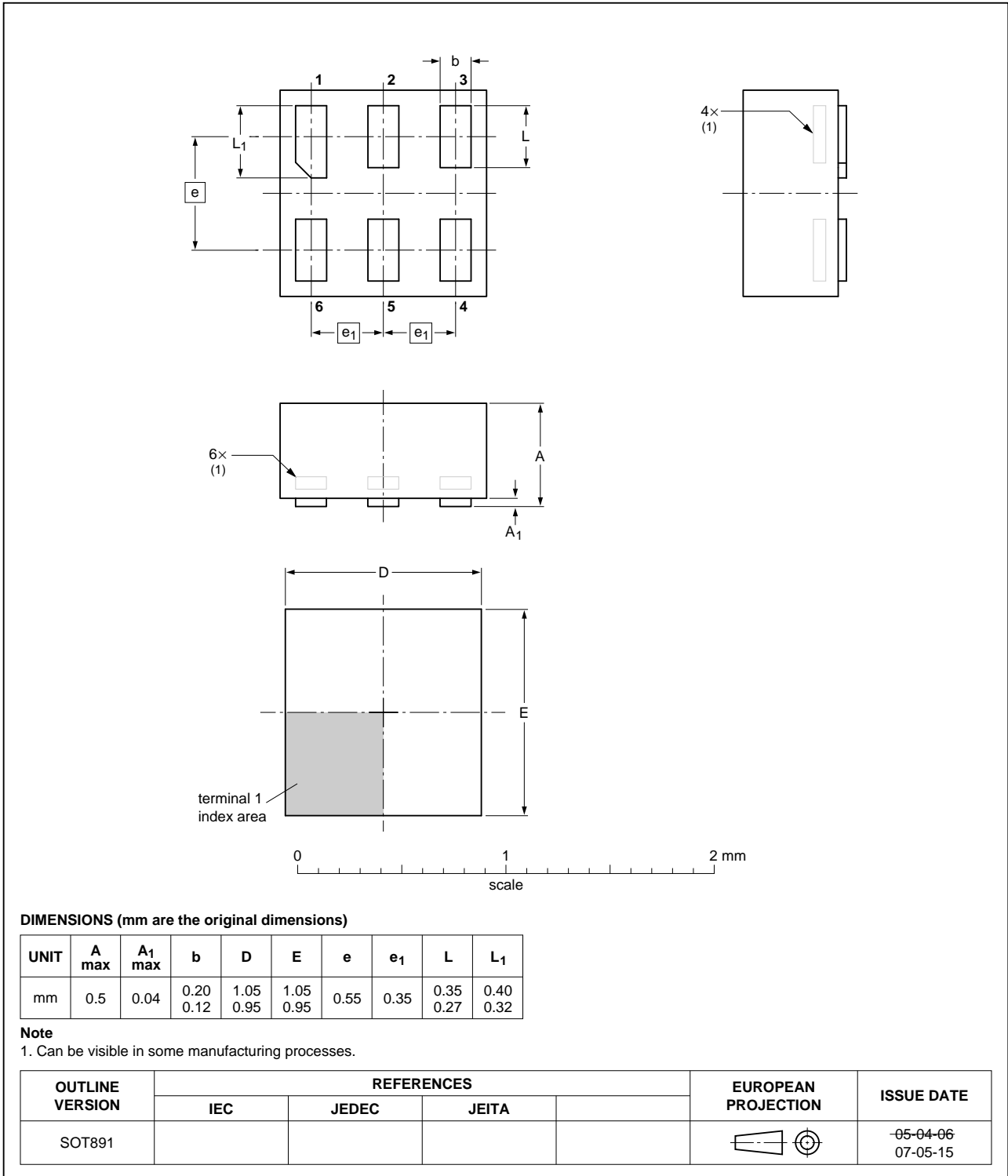


Fig 17. Package outline SOT891 (XSON6)

**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 0.9 x 1.0 x 0.35 mm**

SOT1115

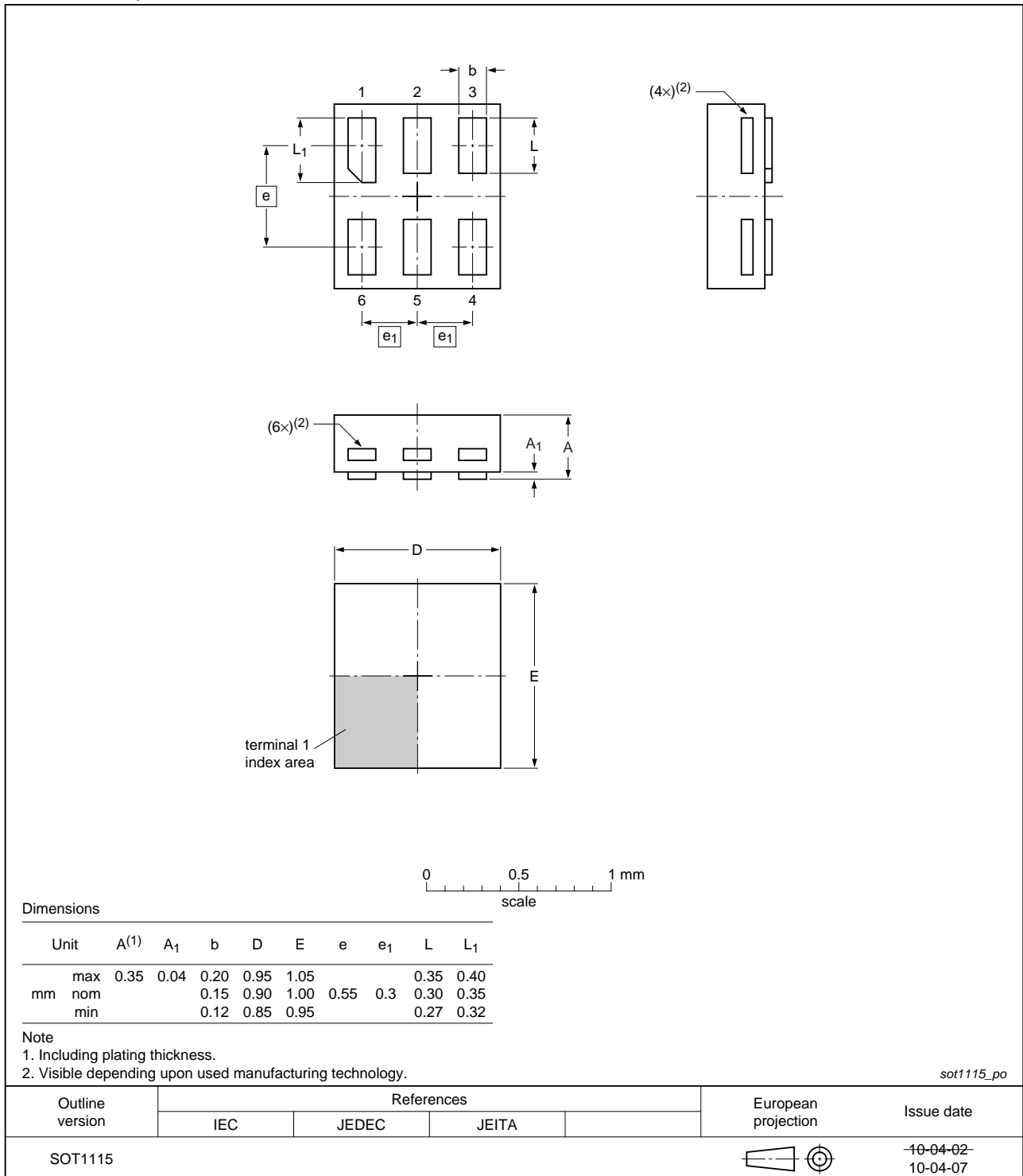


Fig 18. Package outline SOT1115 (XSON6)



**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 1.0 x 1.0 x 0.35 mm**

**SOT1202**



**Fig 19. Package outline SOT1202 (XSON6)**

X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;  
5 terminals; body 0.8 x 0.8 x 0.35 mm

SOT1226

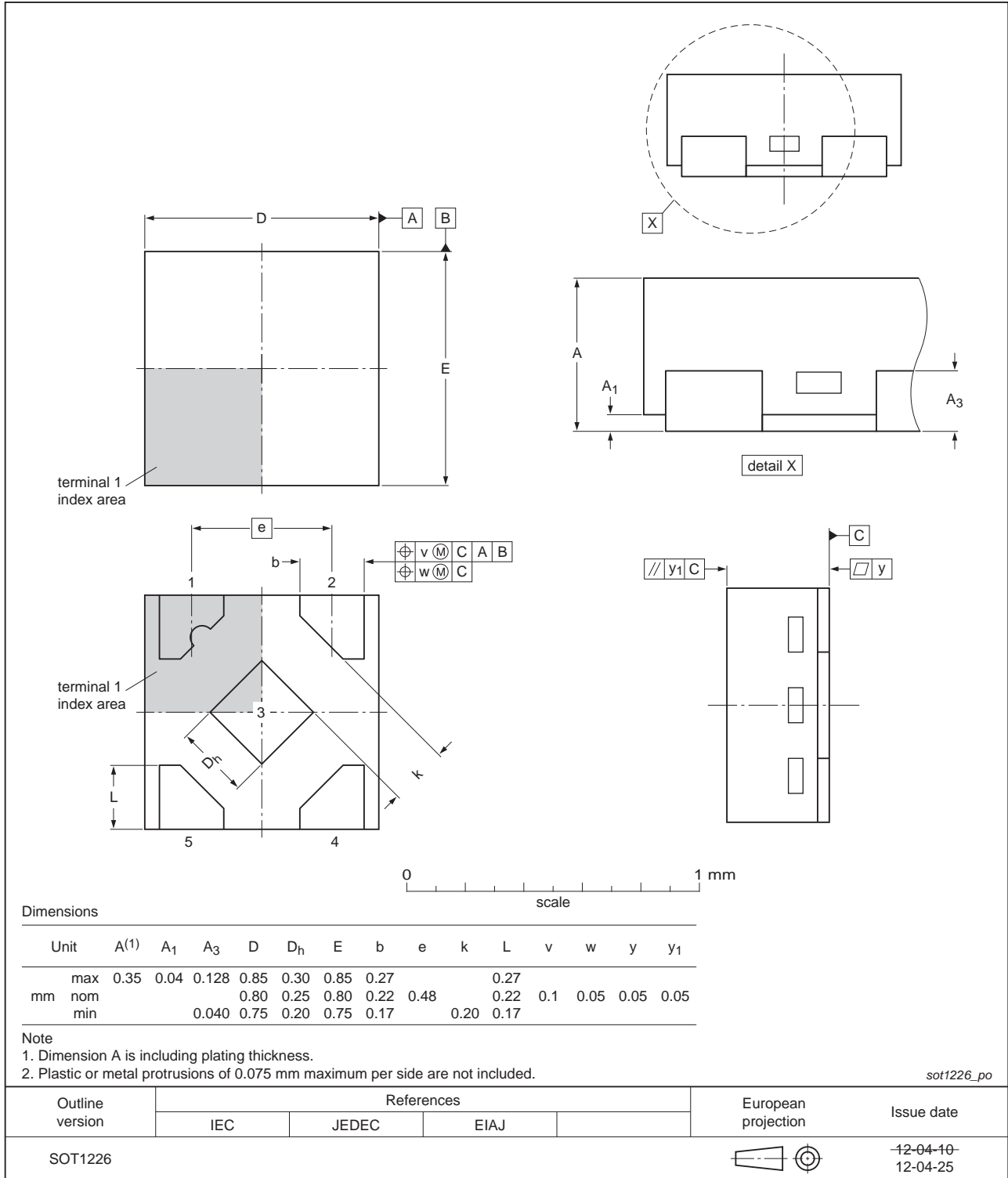


Fig 20. Package outline SOT1226 (X2SON5)

## 18. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 19. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G132 v.5	20120629	Product data sheet	-	74AUP1G132 v.4
Modifications:	<ul style="list-style-type: none"> <li>Added type number 74AUP1G132GX (SOT1226)</li> <li>Package outline drawing of SOT886 (<a href="#">Figure 16</a>) modified.</li> </ul>			
74AUP1G132 v.4	20111124	Product data sheet	-	74AUP1G132 v.3
Modifications:	<ul style="list-style-type: none"> <li>Legal pages updated.</li> </ul>			
74AUP1G132 v.3	20101029	Product data sheet	-	74AUP1G132 v.2
74AUP1G132 v.2	20090615	Product data sheet	-	74AUP1G132 v.1
74AUP1G132 v.1	20061020	Product data sheet	-	-

## 20. Legal information

### 20.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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## 22. Contents

1	General description . . . . .	1
2	Features and benefits . . . . .	1
3	Applications . . . . .	1
4	Ordering information . . . . .	2
5	Marking . . . . .	2
6	Functional diagram . . . . .	2
7	Pinning information . . . . .	3
7.1	Pinning . . . . .	3
7.2	Pin description . . . . .	3
8	Functional description . . . . .	4
9	Limiting values . . . . .	4
10	Recommended operating conditions . . . . .	4
11	Static characteristics . . . . .	5
12	Dynamic characteristics . . . . .	7
13	Waveforms . . . . .	8
14	Transfer characteristics . . . . .	10
15	Waveforms transfer characteristics . . . . .	10
16	Application information . . . . .	12
17	Package outline . . . . .	13
18	Abbreviations . . . . .	19
19	Revision history . . . . .	19
20	Legal information . . . . .	20
20.1	Data sheet status . . . . .	20
20.2	Definitions . . . . .	20
20.3	Disclaimers . . . . .	20
20.4	Trademarks . . . . .	21
21	Contact information . . . . .	21
22	Contents . . . . .	22

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